

Features and Benefits

- Each half-bridge circuit consists of a pre-driver circuit that is completely independent from the others
- Protection against simultaneous high- and low-side turning on
- Bootstrap diodes with series resistors for suppressing inrush current are incorporated
- CMOS compatible input (3.3 to 5 V)
- Designed to minimize simultaneous current through both high- and low-side IGBTs by optimizing gate drive resistors
- Integrated Fast Recovery Diode (FRD) as freewheeling diode for each IGBT
- UVLO protection with auto restart
- Overcurrent protection with off-time period adjustable by an external capacitor
- Fault (FO indicator) signal output at protection activation: UVLO (low side only), OCP, and STP
- Proprietary power DIP package
- UL Recognized Component (File No.: E118037)
- Package: Power DIP

Not to scale

Description

The SCM1103M inverter power module (IPM) device provides a robust, highly-integrated solution for optimally controlling 3-phase motor power inverter systems and variable speed control systems used in energy-conserving designs to drive motors of residential and commercial appliances. These ICs take 85 to 253 VAC input voltage, and 5 A (continuous) output current. They can withstand voltages of up to 600 V (IGBT breakdown voltage).

The SCM1100M series employs a new, small-footprint proprietary DIP package. The IC itself consists of all of the necessary power elements (six IGBTs), pre-drive ICs (three), and freewheeling diodes (six), needed to configure the main circuit of an inverter, as well as a bootstrap circuit (three bootstrap diodes and three boot resistors) as a high-side drive power supply. This enables the main circuit of the inverter to be configured with fewer external components than traditional designs.

Applications include residential white goods (home appliances) and commercial appliance motor control, such as:

- Air conditioner fan motor
- Refrigerator compressor motor
- Washing machine main motor
- Air conditioner compressor motor

Functional Block Diagram

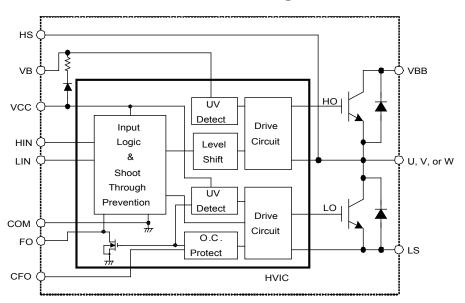


Figure 1. Diagram of one of three phases in the device.

Selection Guide

		IGBT Breakdown Voltage, V _{CES} (min) (V)	IGBT Saturation	Output Current		
Part Number	Packing		Voltage, V _{CE(sat)} (typ) (V)	Continuous, I _O (max) (A)	Pulsed, I _{OP} (max) (A)	
SCM1103M	10 pieces per tube	600	1.7	5	10	

Absolute Maximum Ratings, valid at $T_A = 25^{\circ}C$

Characteristic	Symbol	Remarks	Rating	Units
Supply Voltage	V _{DC}	Between VBB and LS1, LS2, and LS3	450	V
Supply Voltage (Surge)	V _{DC(surge)}	Between VBB and LS1, LS2, and LS3	500	V
IGBT Breakdown Voltage	V _{CES}	V _{CC} = 15 V, I _C = 1 mA, V _{IN} = 0 V	600	V
Logic Supply Voltage	V _{CC}	Between VCC and COM	20	V
Boot-strap Voltage	V _{BS}	Between VB and HS (U,V,W)	20	V
Output Current Continuous		T _{Case} = 25°C	5	Adc
Output Current, Continuous	lo	T _{Case} = 100°C	4.5	Adc
Output Current, Pulsed	I _{OP}	Pulse Width ≤1 ms	10	A
Input Voltage	V _{IN}		-0.5 to 7	V
FO Terminal Voltage	V _{FO}	Between FO and COM	7	V
	P _D	T _{Case} = 25°C, 1 element operation (IGBT)	19.8	W
Maximum Allowable Power Dissipation		T _{Case} = 100°C, 1 element operation (IGBT)	7.9	W
Thermal Desistance, lunction to Coop	R _{(j-c)Q}	1 element operation (IGBT)	6.3	°C/W
Thermal Resistance, Junction-to-Case	R _{(j-c)F}	1 element operation (FRD)	6.5	°C/W
Case Operation Temperature	T _{COP}		-20 to 100	°C
Junction Temperature (IGBT)	TJ		150	°C
Storage Temperature	T _{stg}		-40 to 150	°C
Isolation Voltage	V _{iso}	Between exposed thermal pad and each pin; 1 minute, ac	2000	V _{rms}

Recommended Operating Conditions

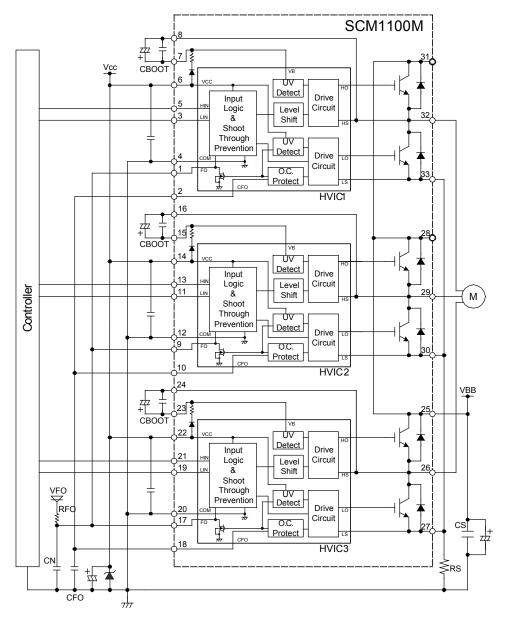
Characteristic	Symbol	Remarks	Min.	Тур.	Max.	Units
Main Supply Voltage	V _{DC}	Between VBB and LS	-	300	400	V
Logic Supply Voltage	V _{CC}	Between VCC and COM	13.5	-	16.5	V
Logic Supply Voltage	V _{BS}	Between VB and HS	13.5	-	16.5	V
Minimum Input Dulco Width	t _{INmin(on)}	On pulse	0.5	_	_	μs
Minimum Input Pulse Width	t _{INmin(off)}	Off pulse	0.5	_	_	μs
Dead Time	t _{dead}		1.5	_	_	μs
FO Pull-up Resistor	R _{FO}		1	-	22	kΩ
CFO Capacitor	C _{FO}		1	_	10	nF
FO Pull-up Voltage	V _{FO}		4.5	_	5.5	V
Bootstrap Capacitor	C _{BOOT}		10	_	220	μF
Shunt Resistor	Rs	For I _P ≤ 10 A	51	_	_	mΩ
PWM Carrier Frequency	f _C		-	_	20	kHz
Junction Temperature	TJ		-	_	125	°C

All performance characteristics given are typical values for circuit or system baseline design only and are at the nominal operating voltage and an ambient temperature, T_A , of 25°C, unless otherwise stated.





Typical Application Diagram



NOTE:

- To use the OCP circuit, an external shunt resistor, RS, is needed. The RS value can be obtained from the formula:
 - $R_{\rm S}(\Omega) = 0.5 (\rm V) / Overcurrent Detection Set Current (A) 0.0024 (\Omega).$
- To avoid malfunction, the wiring between the LS and COM pins should be as short as possible.
- To prevent surge destruction, put a 0.01 to 1 μ F snubber capacitor, CS, in parallel with the electrolytic capacitor.
- To prevent surge destruction, put a 18 to 20 V Zener diode between the VCC and COM pins.
- To prevent surge malfunction, put a 0.01 to 0.1 µF ceramic capacitor between the VCC and COM pins and the VB and HS pins.

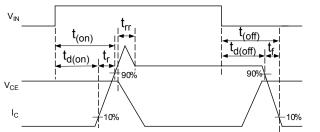




Characteristics	Symbol	Conditions	Min	Тур	Max	Units
Logic Supply Voltage	V _{CC}	Between VCC and COM	13.5	_	16.5	V
Logic Supply Current	I _{CC}	V _{CC} = 15 V, 3 phases operating	_	5	8	mA
Bootstrap Supply Current	I _{BS}	VB – HS = 15 V, one phase operating	_	400	800	μA
	VIH	V _{CC} = 15 V, output on	_	2.0	2.5	V
Input Voltage	V _{IL}	V _{CC} = 15 V, output off	1.0	1.5	_	V
Input Voltage Hysteresis	V _{lhys}	V _{CC} = 15 V	_	0.5	_	V
have the Comment	Іінн	V _{CC} = 15 V, V _{IN} = 5 V	_	50	100	μA
Input Current	I _{ILH}	V _{CC} = 15 V, V _{IN} = 0 V	_	_	2	μA
	U _{VHL}		10.0	_	12.0	V
Undervoltage Lock Out (High Side)	U _{VHH}	V _{CC} = 15 V	10.5	_	12.5	V
	U _{VLL}		10.5	_	12.5	V
Undervoltage Lock Out (Low Side)	U _{VLH}	$V_{\rm CC} = 15 V$	11.0	_	13.0	V
	V _{FOL}		_	_	0.5	V
FO Terminal Output Voltage	V _{FOH}	V_{CC} = 15 V, V_{FO} = 5 V, R_{FO} = 10 k Ω	4.8	-	_	V
Overcurrent Protection Trip Voltage	V _{TRIP}	V _{CC} = 15 V	0.46	0.50	0.54	V
Overcurrent Protection Hold Time	t _P	V _{CC} = 15 V, C _{FO} = 0.0022 μF	2	-	_	ms
Blanking Time	t _{blank}	V _{CC} = 15 V	_	2	_	μs
IGBT Breakdown Voltage	V _{CES}	V _{CC} = 15 V, I _C = 250 μA, V _{IN} = 0 V	600	_	_	V
IGBT Leakage Current	I _{CES}	V _{CC} = 15 V, V _{CE} = 600 V, V _{IN} = 0 V	_	_	1	mA
IGBT Saturation Voltage	V _{CE(sat)}	V _{CC} = 15 V, I _C = 5 A, V _{IN} = 5 V	_	1.7	2.1	V
Diode Forward Voltage	VF	V _{CC} = 15 V, I _F = 10 A, V _{IN} = 0 V	_	1.4	2.0	V
Diode Recovery Time (Bootstrap)	t _{rr}	I _F / I _{RP} = 100 mA/100 mA	_	70	_	ns
Diode Leakage Current (Boot Strap)	I _{IB}	V _R = 600 V	_	5	10	μA
Diode Forward Voltage (Boot Strap)	V _{FB}	I _F = 0.15 A	_	1.1	1.3	V
Diode Series Resistor (Boot Strap)	R _B		17.6	22.0	26.4	Ω
	t _{dH(on)}		_	340	_	ns
	t _{rH}		_	60	_	ns
High Side Switching Time	t _{rrH}	V _{DC} = 300 V, V _{CC} = 15 V, I _C = 5 A, inductive load; HIN = 0→5 V or 5→0 V	_	80	_	ns
	t _{dH(off)}		_	430	_	ns
	t _{fH}		_	240	-	ns
	t _{dL(on)}	− V _{DC} = 300 V, V _{CC} = 15 V, I _C = 5 A, inductive load; LIN = 0→5 V or 5→0 V	_	380	-	ns
	t _{rL}		_	90	_	ns
Low Side Switching Time	t _{rrL}		_	100	_	ns
	t _{dL(off)}		_	500	_	ns
	t _{fL}		_	220	_	ns

ELECTRICAL CHARACTERISTICS, valid at T_A=25°C, unless otherwise noted

Switching Timing Definitions



SanKen

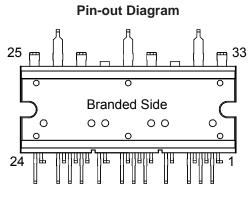
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Input Output Truth Table

HIN	LIN	OUT
L	L	High Z
L	Н	L
Н	L	Н
Н	Н	High Z

High Z = High Impedance





(Bottom View)

Terminal List Table

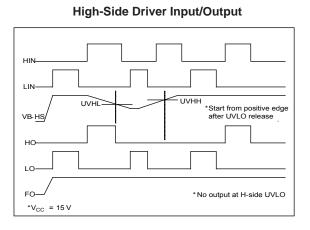
Name	Number	Function
1	FO1	U phase fault output for overcurrent and UVLO detected
2	CFO1	Capacitor for U phase overcurrent protection hold time
3	LIN1	Signal input for low-side U phase (active high)
4	COM1	Supply ground for U phase IC
5	HIN1	Signal input for high-side U phase (active high)
6	VCC1	Supply voltage for U phase IC
7	VB1	High-side floating supply voltage for U phase
8	HS1	High-side floating supply ground for U phase
9	FO2	V phase fault output for overcurrent and UVLO detected
10	CFO2	Capacitor for V phase overcurrent protection hold time
11	LIN2	Signal input for low-side V phase (active high)
12	COM2	Supply ground for V phase IC
13	HIN2	Signal input for high-side V phase (active high)
14	VCC2	Supply voltage for V phase IC
15	VB2	High-side floating supply voltage for V phase
16	HS2	High-side floating supply ground for V phase
17	FO3	W phase fault output for overcurrent and UVLO detected
18	CFO3	Capacitor for W phase overcurrent protection hold time
19	LIN3	Signal input for low-side W phase (active high)
20	COM3	Supply ground for W phase IC
21	HIN3	Signal input for high-side W phase (active high)
22	VCC3	Supply voltage for W phase IC
23	VB3	High-side floating supply voltage for W phase
24	HS3	High-side floating supply ground for W phase
25	VBB	Positive DC bus supply voltage
26	W	Output for W phase
27	LS3	Negative DC bus supply ground for W phase
28	VBB	Cut-pin (positive DC bus supply voltage)
29	V	Output for V phase
30	LS2	Negative DC bus supply ground for V phase
31	VBB	Cut-pin (positive DC bus supply voltage)
32	U	Output for U phase
33	LS1	Negative DC bus supply ground for U phase

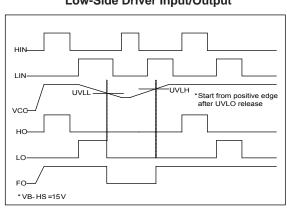




High Voltage 3-Phase Motor Driver

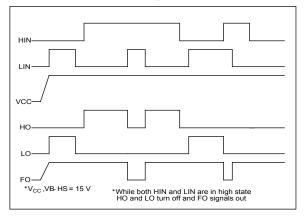
Timing Diagrams



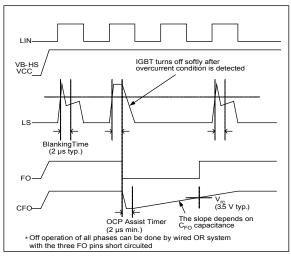


Low-Side Driver Input/Output

Shoot-Through Prevention



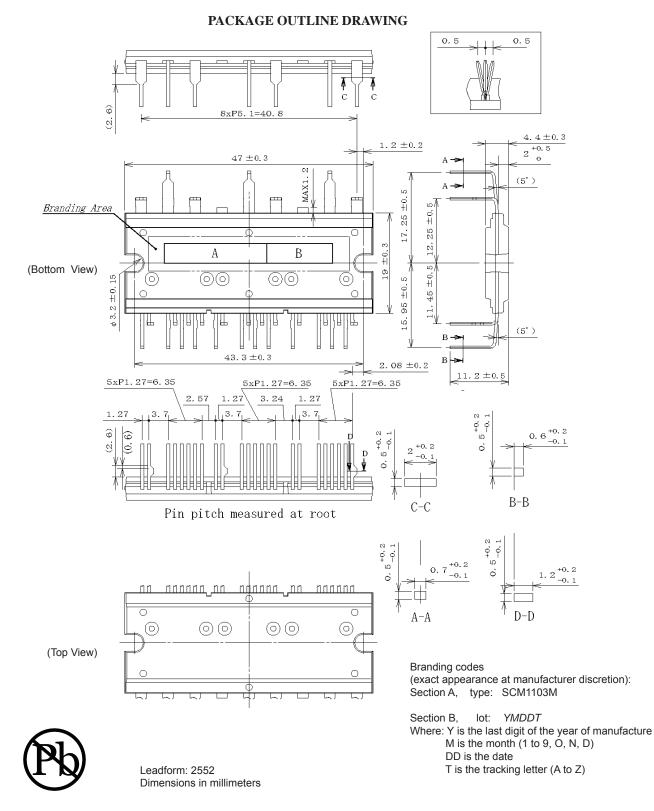
Overcurrent Protection







High Voltage 3-Phase Motor Driver



Leadframe plating Pb-free. Device composition complies with the RoHS directive.

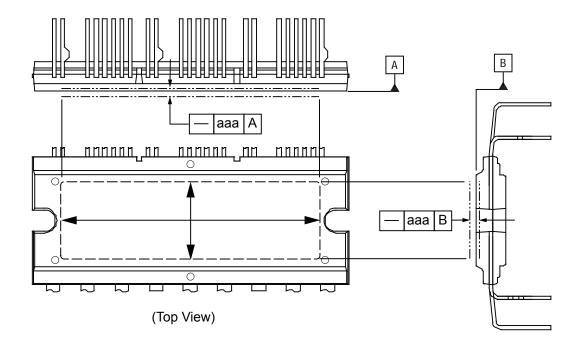


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MECHANICAL CHARACTERISTICS

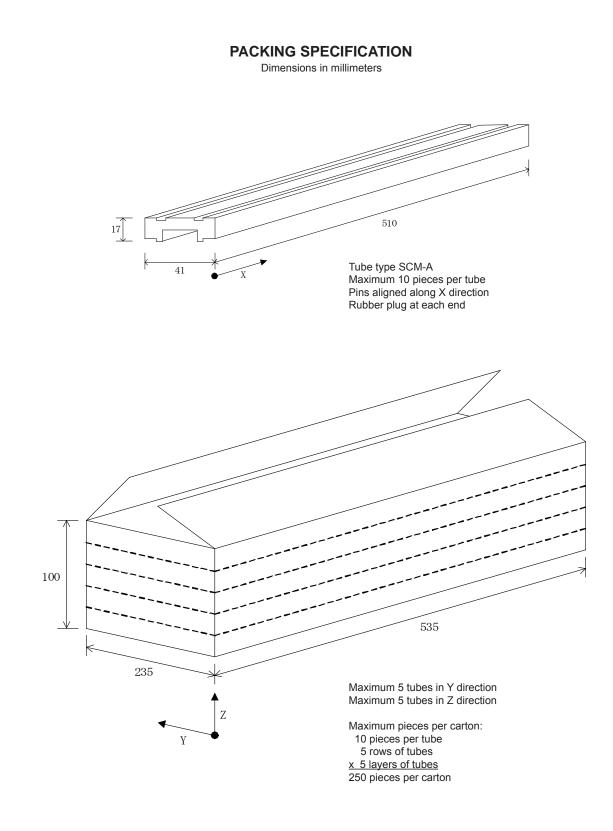
Characteristic	Remarks	Min.	Тур.	Max.	Units
Heatsink Mounting Screw Torque	Use one M3 screw each end	58.8	_	78.4	N•cm
Heatsink Mounting Sciew Torque		6.0	_	8.0	kgf•cm
Flatness of Heatsink Attachment Area	Refer to figure below (aaa)	-50	_	100	μm
Package Weight		-	13.5	_	g







High Voltage 3-Phase Motor Driver





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High Voltage 3-Phase Motor Driver



WARNING — These devices are designed to be operated at lethal voltages and energy levels. Circuit designs that embody these components must conform with applicable safety requirements. Precautions must be taken to prevent accidental contact with power-line potentials. Do not connect grounded test equipment.

The use of an isolation transformer is recommended during circuit development and breadboarding.

Because reliability can be affected adversely by improper storage environments and handling methods, please observe the following cautions.

Cautions for Storage

- Ensure that storage conditions comply with the standard temperature (5°C to 35°C) and the standard relative humidity (around 40 to 75%); avoid storage locations that experience extreme changes in temperature or humidity.
- Avoid locations where dust or harmful gases are present and avoid direct sunlight.
- Reinspect for rust on leads and solderability of product that has been stored for a long time.

Cautions for Testing and Handling

When tests are carried out during inspection testing and other standard test periods, protect the product from power surges from the testing device, shorts between adjacent product packages, and shorts to the heatsink.

Remarks About Using Silicone Grease with a Heatsink

- Ensure there are no foreign objects between the heatsink and thermal pad; only silicone thermal grease is allowed.
- When silicone grease is used in mounting this product with a heatsink, grease shall be applied evenly and thinly. If more silicone grease than required is applied, it may produce stress.
- Volatile-type silicone greases may permeate the product and produce cracks after long periods of time, resulting in reduced heat radiation effect, and possibly shortening the lifetime of the product.
- Hard silicone greases may cause cracks in the product when screwing the product to a heatsink.

 Our recommended silicone greases for heat radiation purposes, which will not cause any adverse effect on the product life, are indicated below:

Туре	Suppliers
G746	Shin-Etsu Chemical Co., Ltd.
YG6260	Momentive Performance Materials
SC102	Dow Corning Toray Silicone Co., Ltd.

Soldering

- When soldering the product, please be sure to minimize the working time, within the following limits: 260±5°C 10 s
 - 380±5°C 5 s
- Soldering iron should be at a distance of at least 1.5 mm from the body of the product

Electrostatic Discharge

- When handling the product, operator must be grounded. Grounded wrist straps worn should have at least 1 MΩ of resistance to ground to prevent shock hazard.
- Workbenches where the product is handled should be grounded and be provided with conductive table and floor mats.
- When using measuring equipment such as a curve tracer, the equipment should be grounded.
- When soldering the product, the head of soldering irons or the solder bath must be grounded in other to prevent leak voltages generated by them from being applied to the product.
- The product should always be stored and transported in our shipping containers or conductive containers, or be wrapped in aluminum foil.





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